

13. The atomic layer etching method according to claim 10, wherein, the reaction gas in step S2 is at least one of CF₄, CHF₃, CH₂F₂, CH₃F, Cl₂, HF, HCl, HBr, SF₆, NF₃, Br₂, BCl₃, SiCl₄, and O₂.

14. The atomic layer etching method according to claim 13, wherein, the reaction gas in step S2 is Cl₂, and has a flow rate ranging from 5 sccm to 200 sccm.

15. The atomic layer etching method according to claim 10, wherein, the reaction gas in step S6 is an inert gas.

16. The atomic layer etching method according to claim 15, wherein, the inert gas in step S6 is at least one of He, Ni, Ar, Kr, and Xe.

17. The atomic layer etching method according to claim 16, wherein, the reaction gas in step S6 is He, and has a flow rate ranging from 10 sccm to 200 sccm.

18. The atomic layer etching method according to claim 10, wherein, a first gas inlet is provided at the top of the upper chamber, and the reaction gas enters the reaction chamber via the first gas inlet; a second gas inlet is provided on the side of the upper chamber, and the purge gas enters the reaction chamber via the second gas inlet.

19. The atomic layer etching method according to claim 10, wherein, the baffle assembly comprises three baffles, which are arranged at a certain interval in a vertical direction, and baffles at the top and at the bottom among the three baffles are grounded, and a baffle in the middle among the three baffles is connected to a direct current (DC) bias power supply.

20. The atomic layer etching method according to any one of claims 10 to 19,